

TC74HC32AP, TC74HC32AF, TC74HC32AFN

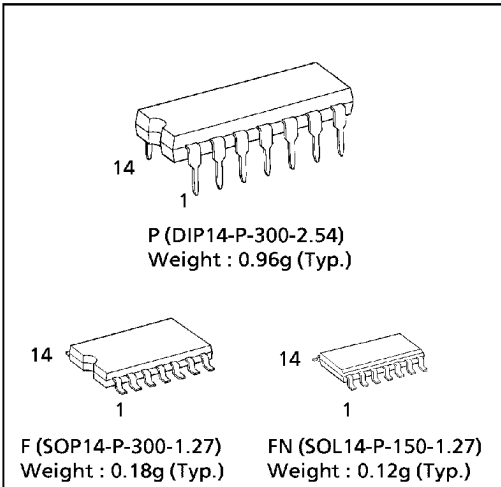
QUAD 2-INPUT OR GATE

(Note) The JEDEC SOP (FN) is not available in Japan.

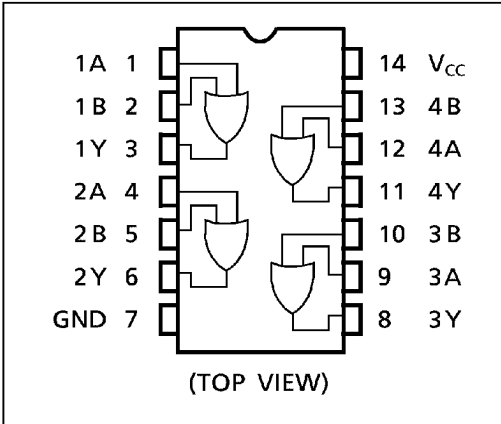
The TC74HC32A is a high speed CMOS 2-INPUT OR GATE fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 2 stages including buffer output, which provide high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES :

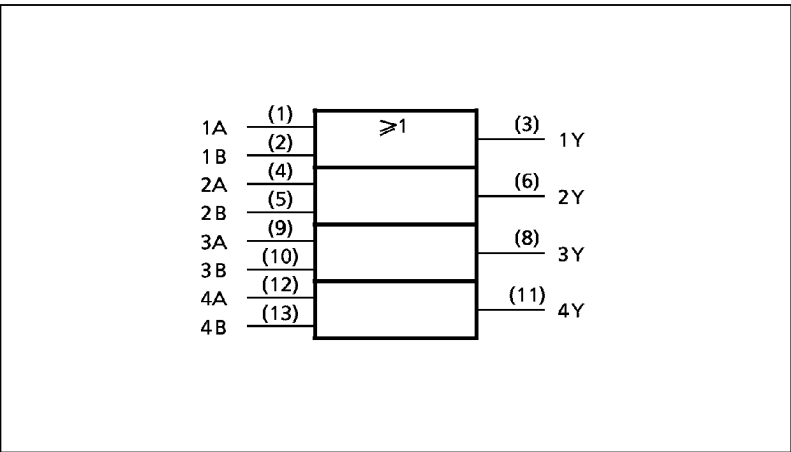
- High Speed..... $t_{pd} = 6ns$ (typ.) at $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 1\mu A$ (max.) at $T_a = 25^\circ C$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min.)
- Output Drive Capability..... 10 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 4mA$ (min.)
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range.... V_{CC} (opr.) = 2V~6V
- Pin and Function Compatible with 74LS32



PIN ASSIGNMENT



IEC LOGIC SYMBOL



TRUTH TABLE

A	B	Y
H	H	H
L	H	H
H	L	H
L	L	L

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7$	V
DC Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} / Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	$^{\circ}\text{C}$

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	$2 \sim 6$	V
Input Voltage	V_{IN}	$0 \sim V_{CC}$	V
Output Voltage	V_{OUT}	$0 \sim V_{CC}$	V
Operating Temperature	T_{opr}	$-40 \sim 85$	$^{\circ}\text{C}$
Input Rise and Fall Time	t_r, t_f	$0 \sim 1000$ ($V_{CC} = 2.0\text{V}$) $0 \sim 500$ ($V_{CC} = 4.5\text{V}$) $0 \sim 400$ ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	V_{IH}		2.0	1.50	—	—	1.50	—	V	
			4.5	3.15	—	—	3.15	—		
			6.0	4.20	—	—	4.20	—		
Low - Level Input Voltage	V_{IL}		2.0	—	—	0.50	—	0.50	V	
			4.5	—	—	1.35	—	1.35		
			6.0	—	—	1.80	—	1.80		
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
				4.5	4.4	4.5	—	4.4	—	
				6.0	5.9	6.0	—	5.9	—	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
				4.5	—	0.0	0.1	—	0.1	
				6.0	—	0.0	0.1	—	0.1	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	1.0	—	10.0	μA	

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH}		—	4	8	ns
	t_{THL}					
Propagation Delay Time	t_{pLH}		—	6	12	ns
	t_{pHL}					

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^\circ\text{C}$			$T_a = -40\text{--}85^\circ\text{C}$		UNIT	
			$V_{CC}(\text{V})$	MIN.	TYP.	MAX.	MIN.		MAX.
Output Transition Time	t_{TLH}		2.0	—	25	75	—	95	ns
	t_{THL}		4.5	—	7	15	—	19	
			6.0	—	6	13	—	16	
Propagation Delay Time	t_{pLH}		2.0	—	24	75	—	95	ns
	t_{pHL}		4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Input Capacitance	C_{IN}		—	5	10	—	10	pF	
Power Dissipation Capacitance	$C_{PD} (1)$		—	21	—	—	—	pF	

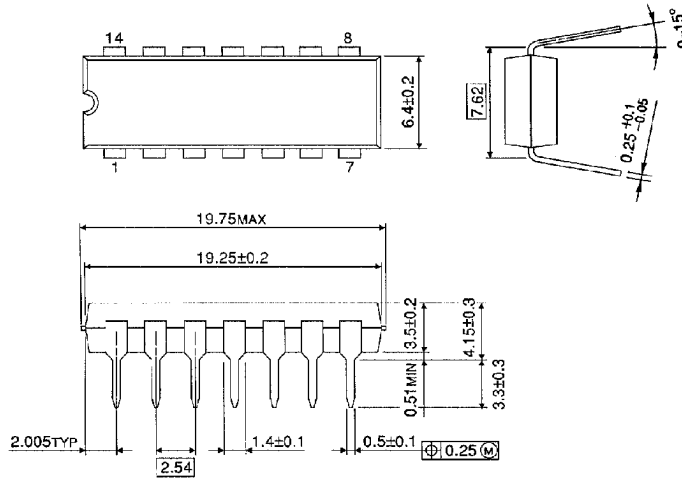
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (per Gate)}$$

DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

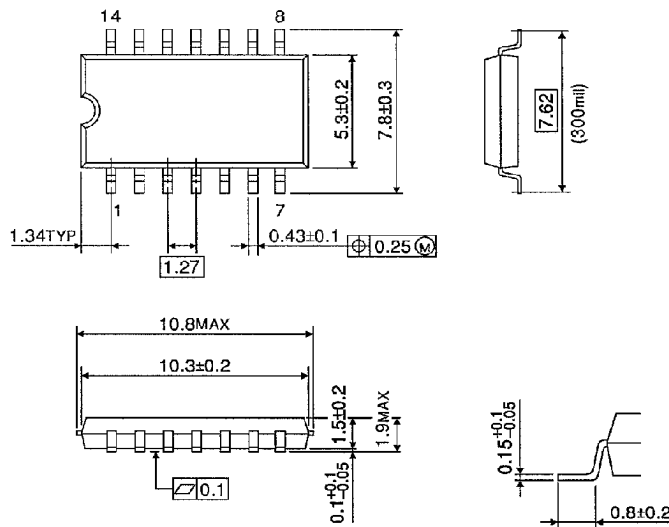
Unit in mm



Weight : 0.96g (Typ.)

SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

Unit in mm

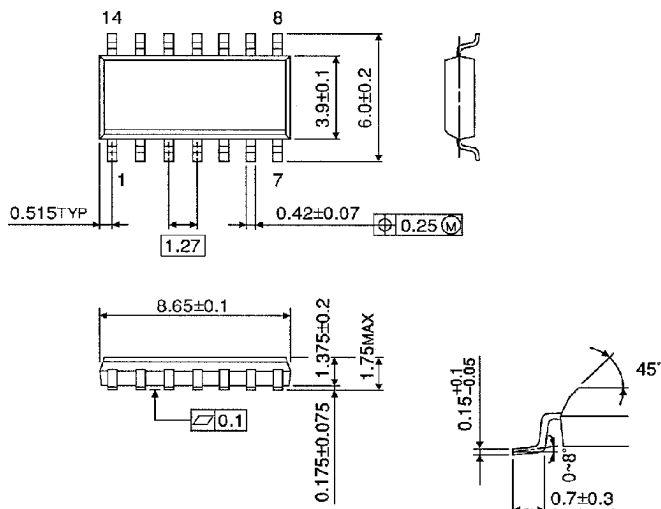


Weight : 0.18g (Typ.)

SOP 14PIN (150mil BODY) OUTLINE DRAWING (SOL14-P-150 -1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.12g (Typ.)